

Features

BV_{CEO}	60 V
I_C (max)	0.6 A
H_{FE} at 10 V - 150 mA	> 100
Operating temperature range	-65°C to +200°C

- Hi-Rel PNP bipolar transistor
- Linear gain characteristics
- ESCC qualified
- European preferred part list - EPPL
- Radiation level: lot specific total dose contact marketing for specified level

Description

The 2N2905AHR is a silicon planar epitaxial PNP transistor in a TO-39 package. It is specifically designed for aerospace Hi-Rel applications, and ESCC qualified in accordance with the 5202-002 specification. In case of discrepancies between this datasheet and ESCC detailed specification, the latter prevails.

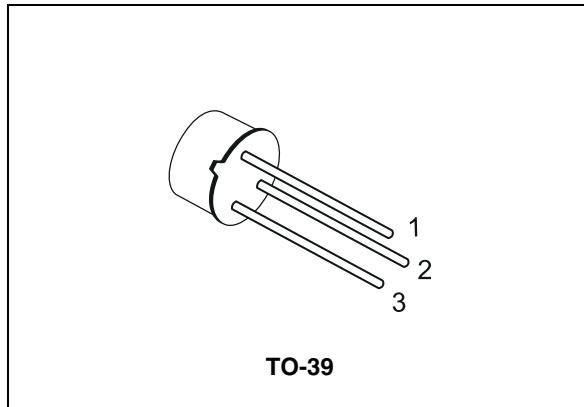


Figure 1. Internal schematic diagram

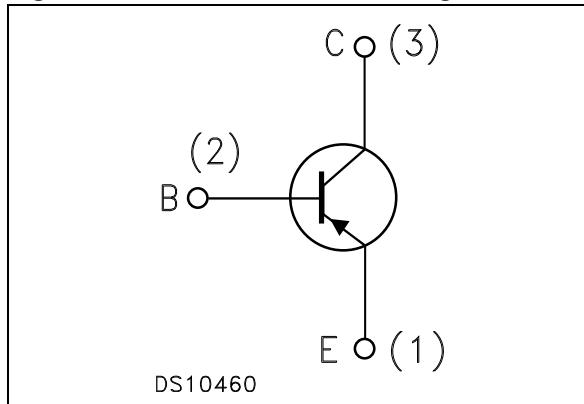


Table 1. Device summary

Order codes	Package	Lead finish	Marking	Type	EPPL	Packaging
2N2905AHR	TO-39	Gold Solder Dip	520200201 520200202	ESCC Flight	Yes	Strip pack
2N2905AHR	TO-39	Gold	2N2905AT1	Engineering model		Strip pack

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base voltage ($I_E = 0$)	-60	V
V_{CEO}	Collector-emitter voltage ($I_B = 0$)	-60	V
V_{EBO}	Emitter-base voltage ($I_C = 0$)	-5	V
I_C	Collector current	-0.6	A
P_{TOT}	Total dissipation at $T_{amb} \leq 25 \text{ }^{\circ}\text{C}$	0.6	W
	Total dissipation at $T_c \leq 25 \text{ }^{\circ}\text{C}$	3	W
T_{STG}	Storage temperature	-65 to 200	$^{\circ}\text{C}$
T_J	Max. operating junction temperature	200	$^{\circ}\text{C}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case	58	$^{\circ}\text{C}/\text{W}$
R_{thJA}	Thermal resistance junction-ambient	291	$^{\circ}\text{C}/\text{W}$

2 Electrical characteristics

$T_{case} = 25^\circ\text{C}$ unless otherwise specified.

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector-base cut-off current ($I_E = 0$)	$V_{CB} = -50\text{ V}$ $V_{CB} = -50\text{ V}, T_C = 150^\circ\text{C}$			-10 -10	nA μA
$V_{(BR)CBO}$	Collector-base breakdown voltage ($I_E = 0$)	$I_C = -10\text{ }\mu\text{A}$	-60			V
$V_{(BR)CEO}^{(1)}$	Collector-emitter breakdown voltage ($I_B = 0$)	$I_C = -10\text{ mA}$	-60			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage ($I_C = 0$)	$I_E = -10\text{ }\mu\text{A}$	-5			V
$V_{CE(sat)}^{(1)}$	Collector-emitter saturation voltage	$I_C = -150\text{ mA}, I_B = -15\text{ mA}$			-0.4	V
$V_{BE(sat)}^{(1)}$	Base-emitter saturation voltage	$I_C = -150\text{ mA}, I_B = -15\text{ mA}$			-1.3	V
$h_{FE}^{(1)}$	DC current gain	$I_C = -0.1\text{ mA}, V_{CE} = -10\text{ V}$ $I_C = -1\text{ mA}, V_{CE} = -10\text{ V}$ $I_C = -150\text{ mA}, V_{CE} = -10\text{ V}$ $I_C = -500\text{ mA}, V_{CE} = -10\text{ V}$	75 100 100 50		300	
h_{fe}	Small signal current gain	$V_{CE} = -20\text{ V}, I_C = -50\text{ mA}$ $f = 100\text{ MHz}$	2			
C_{CBO}	Output capacitance ($I_E = 0$)	$V_{CB} = -10\text{ V}$ $100\text{ kHz} \leq f \leq 1\text{ MHz}$			8	pF
t_{on}	Turn-on time	$V_{CC} = -30\text{ V}, I_C = -150\text{ mA}$ $I_{B1} = -15\text{ mA}$			45	ns
t_{off}	Turn-off time	$V_{CC} = -30\text{ V}, I_C = -150\text{ mA}$ $I_{B1} = -I_{B2} = -15\text{ mA}$			300	ns

1. Pulsed duration = 300 μs , duty cycle $\leq 1.5\%$

2.1 Electrical characteristics (curves)

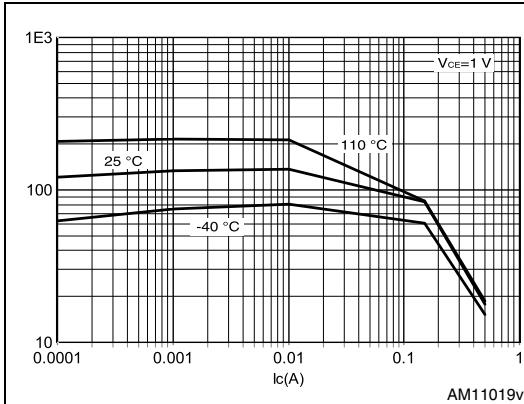
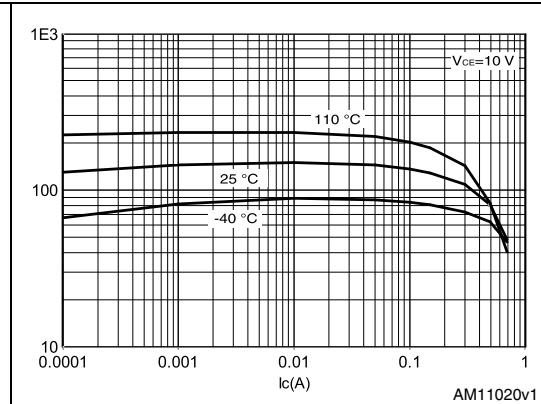
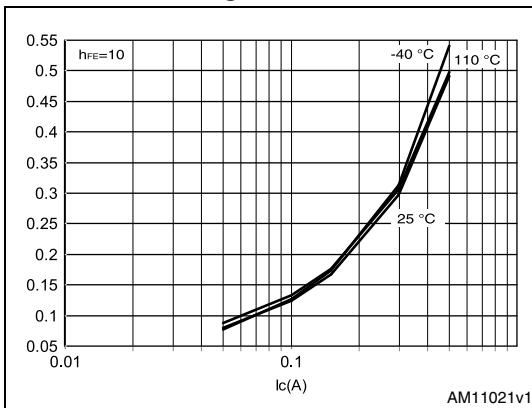
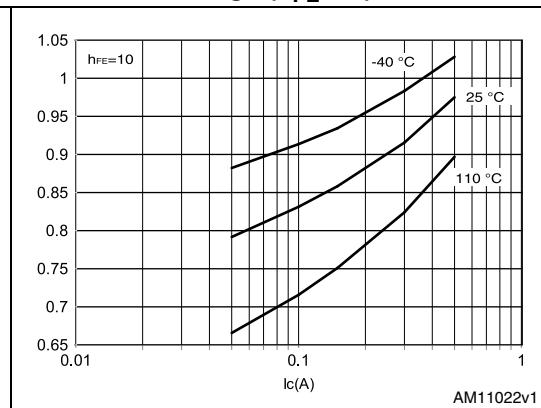
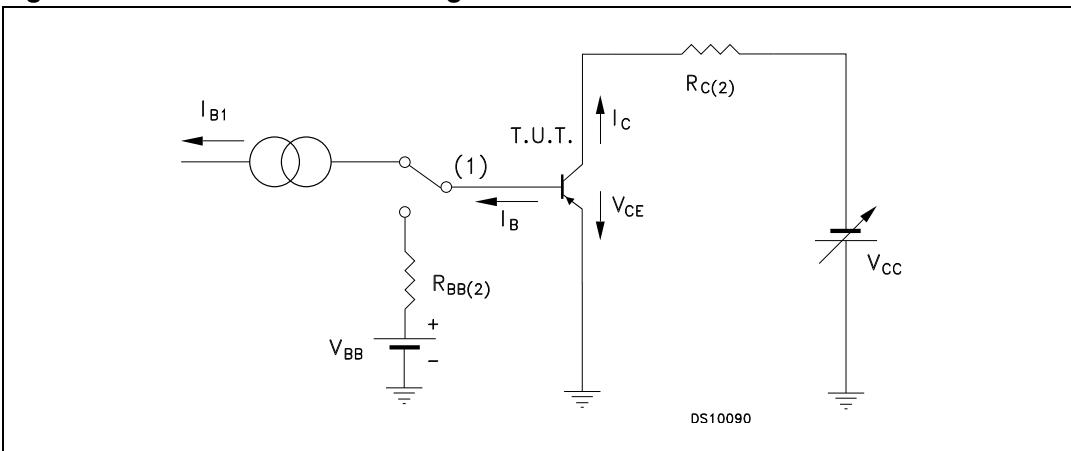
Figure 2. DC current gain ($V_{CE}=1$ V)Figure 3. DC current gain ($V_{CE}=10$ V)

Figure 4. Collector emitter saturation voltage

Figure 5. Base emitter saturation voltage ($h_{FE}=10$)

2.2 Test circuit

Figure 6. Resistive load switching test circuit



1. Fast electronic switch
2. Non-inductive resistor

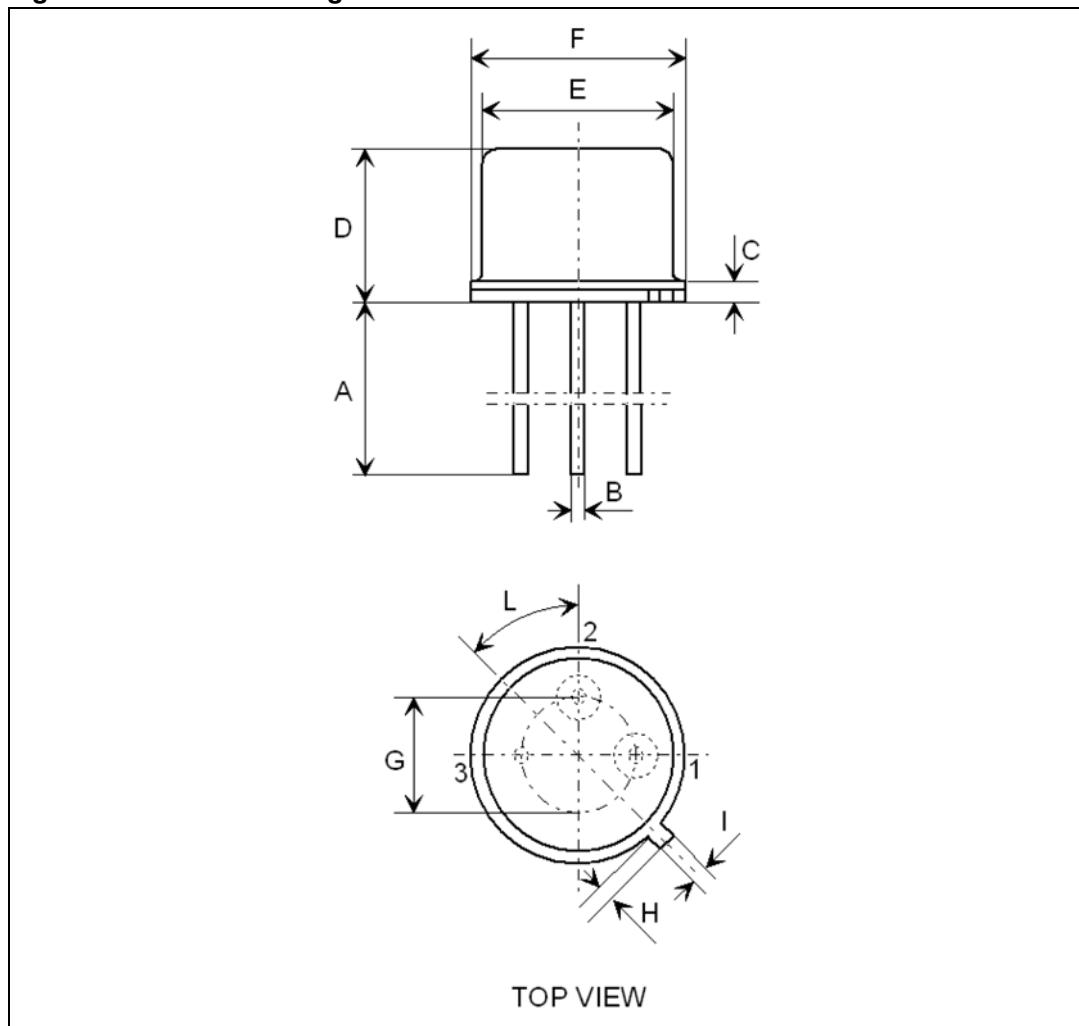
3 Package mechanical data

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Table 5. TO-39 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A		12.70	14.20
B		0.40	0.49
C		0.58	0.74
D		6.00	6.40
E		8.15	8.25
F		9.10	9.20
G		4.93	5.23
H		0.85	0.95
I		0.75	0.85
L		42°	48°

Figure 7. TO-39 drawing



4 Revision history

Table 6. Document revision history

Date	Revision	Changes
14-Jan-2009	1	Initial release.
05-Jan-2010	2	Modified Table 1 on page 1 .
11-Oct-2012	3	Minor text changes. Section 2.1: Electrical characteristics (curves) has been added.
08-Jan-2013	4	Updated Figure 1: Internal schematic diagram .

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